Switch-mode Power Rectifier

This switch-mode power rectifier uses the Schottky Barrier principle with a platinum barrier metal. This state-of-the-art device has the following features:

Features

- Low Forward Voltage
- 175°C Operating Junction Temperature
- Low Power Loss/High Efficiency
- High Surge Capacity
- This is a Pb-Free Device

Applications

- Power Supply Output Rectification
- Power Management

Mechanical Characteristics

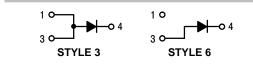
- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 1.7 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds



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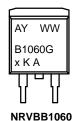
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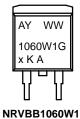
SCHOTTKY BARRIER RECTIFIER 10 AMPERES, 60 VOLTS





MARKING DIAGRAMS





= Assembly Location

= Year WW = Work Week G = Pb-Free Package xKA = Diode Polarity = N or A

ORDERING INFORMATION

Device	Package	Shipping [†]
NRVBB1060T4G	D ² PAK (Pb-Free)	800/Tape & Reel
NRVBB1060W1T4G (In Development)	D ² PAK (Pb-Free)	800/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

This document contains information on some products that are still under development. ON Semiconductor reserves the right to change or discontinue these products without notice.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	60	V
Average Rectified Forward Current (Rated V _R) T _C = 133°C	I _{F(AV)}	10	Α
Peak Repetitive Forward Current (Rated V _R , Square Wave, 20 kHz) T _C = 133°C	I _{FRM}	20	А
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I _{FSM}	150	А
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz)	I _{RRM}	0.5	Α
Operating Junction Temperature (Note 1)	TJ	-65 to +175	°C
Storage Temperature	T _{stg}	- 65 to +175	°C
Voltage Rate of Change (Rated V _R)	dv/dt	10,000	V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction–to–Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Maximum Thermal Resistance, Junction-to-Case	R _{θJC}	2.0	°C/W
Maximum Thermal Resistance, Junction-to-Ambient	$R_{ heta JA}$	60	°C/W
ELECTRICAL CHARACTERISTICS			

Maximum Instantaneous Forward Voltage (Note 2) $ \begin{aligned} &(i_F=10 \text{ Amps, } T_C=125^{\circ}\text{C}) \\ &(i_F=10 \text{ Amps, } T_C=25^{\circ}\text{C}) \\ &(i_F=20 \text{ Amps, } T_C=125^{\circ}\text{C}) \\ &(i_F=20 \text{ Amps, } T_C=25^{\circ}\text{C}) \end{aligned} $	VF	0.7 0.8 0.85 0.95	V
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, T_C = 125°C) (Rated dc Voltage, T_C = 25°C)	i _R	25 0.10	mA

^{2.} Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.

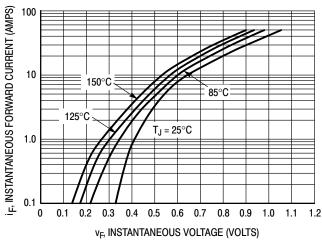


Figure 1. Typical Forward Voltage

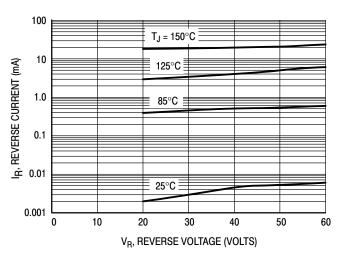


Figure 2. Typical Reverse Current

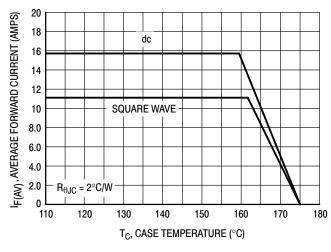


Figure 3. Current Derating, Case

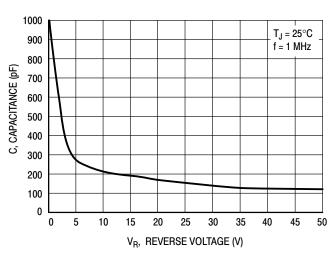


Figure 4. Typical Capacitance

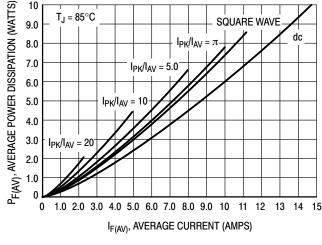


Figure 5. Typical Forward Power Dissipation

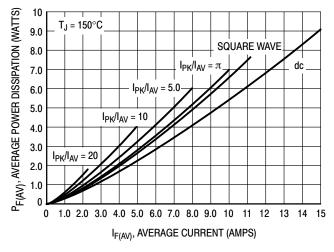


Figure 6. Typical Forward Power Dissipation

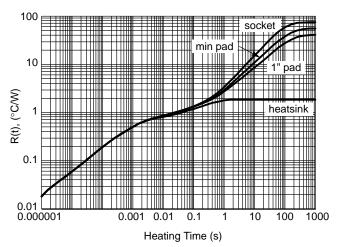
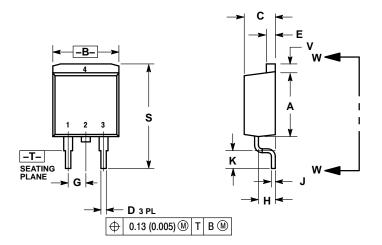


Figure 7. Single-Pulse Transient Response Curves, Various Mounting Conditions

PACKAGE DIMENSIONS

D²PAK 3 CASE 418B-04 **ISSUE L**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

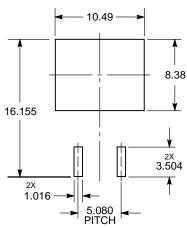
	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.340	0.380	8.64	9.65	
В	0.380	0.405	9.65	10.29	
C	0.160	0.190	4.06	4.83	
D	0.020	0.035	0.51	0.89	
Е	0.045	0.055	1.14	1.40	
F	0.310	0.350	7.87	8.89	
G	0.100 BSC		2.54 BSC		
Η	0.080	0.110	2.03	2.79	
J	0.018	0.025	0.46	0.64	
K	0.090	0.110	2.29	2.79	
L	0.052	0.072	1.32	1.83	
М	0.280	0.320	7.11	8.13	
N	0.197 REF		5.00 REF		
Р	0.079 REF		2.00 REF		
R	0.039	REF	0.99 REF		
S	0.575	0.625	14.60	15.88	
٧	0.045	0.055	1.14	1.40	

STYLE 3: PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE

STYLE 6: PIN 1. NO CONNECT 2. CATHODE 3. ANODE 4. CATHODE

VARIABLE CONFIGURATION ZONE М M M VIEW W-W VIEW W-W VIEW W-W

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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